

SEMICONDUCTOR DEVICE BONDING WIRE

Abstract

5 It is an object of the present invention to provide a
copper-based bonding wire in which the material cost is low and
ball bondability, reliability in a heat cycle test or reflow
test and storage life are excellent and its application is
possible for a fine wire used for a fine pitch. The bonding wire
10 includes a core material with copper as its component and an
outer layer which is provided on the core material and with
difference in component and/or composition from those of the
core material. The outer layer is 0.021 to 0.12 μm in thickness.